TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

T C 4 S U 6 9 F

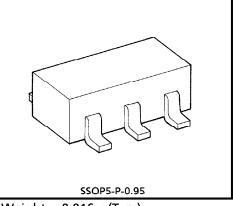
INVERTER GATE

The TC4SU69F is single inverter.

Therefore, this is suitable for the applications of C, R oscillator circuits, crystal oscillator circuits and linear amplifiers in addition to its application as inverters.

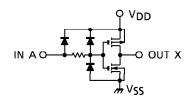
MAXIMUM RATINGS (Ta = 25°C)

	,		
CHARACTERISTIC	SYMBOL	RATING	UNIT
DC Supply Voltage	V_{DD}	Vss - 0.5~Vss + 20	V
Input Voltage	V _{IN}	$V_{SS} - 0.5 \sim V_{DD} + 0.5$	V
Output Voltage	Vout	$V_{SS} - 0.5 \sim V_{DD} + 0.5$	V
DC Input Current	lIN	± 10	mA
Power Dissipation	PD	200	mW
Operating Temperature Range	T _{opr}	- 40~85	°
Storage Temperature Range	T _{stg}	- 65~150	°C
Lead Temperature (10s)	TL	260	°C

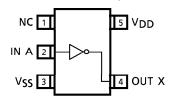


Weight: 0.016g (Typ.)

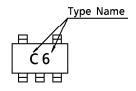
LOGIC DIAGRAM



PIN CONFIGURATION (TOP VIEW)



Marking



961001EBA2

[●] TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent products specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook.

RECOMMENDED OPERATING CONDITIONS $(V_{SS} = 0V)$

CHARACTERISTIC	SYMBOL		MIN.	TYP.	MAX.	UNIT
DC Supply Voltage	V_{DD}	_	3	_	18	V
Input Voltage	V _{IN}		0		V_{DD}	V

STATIC ELECTRICAL CHARACTERISTICS $(V_{SS} = 0V)$

CHARACTERISTIC SY		TEST CONDITION	V_{DD}	– 40°C		25°C			85°C		UNIT
BOL	TEST CONDITION	(V)	MIN.	MAX.	MIN.	TYP.	MAX.	MIN.	MAX.	OINII	
High-Level Output Voltage	Voн	$ I_{OUT} < 1\mu A$ $V_{IN} = V_{SS}$	5 10 15	4.95 9.95 14.95	_	4.95 9.95 14.95	10.00	_	4.95 9.95 14.95	 	
Low-Level Output Voltage	VOL	I _{OUT} <1μΑ V _{IN} = V _{DD}	5 10 15	— — —	0.05 0.05 0.05	— —	0.00 0.00 0.00	0.05 0.05	— — —	0.05 0.05 0.05	V
Output High Current	ЮН	V _{OH} = 4.6V V _{OH} = 2.5V V _{OH} = 9.5V V _{OH} = 13.5V V _{IN} = V _{SS}	5 5 10 15	- 0.61 - 2.5 - 1.5 - 4.0		- 0.51 - 2.1 - 1.3 - 3.4	- 9.0	_ _ _	- 0.42 - 1.7 - 1.1 - 2.8	_ _	mA
Output Low Current	lOL	$V_{OL} = 0.4V$ $V_{OL} = 0.5V$ $V_{OL} = 1.5V$ $V_{IN} = V_{DD}$	5 10 15	0.61 1.5 4.0	_	0.51 1.3 3.4	3.2	_	0.42 1.1 2.8	—	
Input High Voltage	V _{IH}	$V_{OUT} = 0.5V$ $V_{OUT} = 1.0V$ $V_{OUT} = 1.5V$ $ I_{OUT} < 1\mu A$	5 10 15	4.0 8.0 12.0	_	4.0 8.0 12.0	_		4.0 8.0 12.0	 	V
Input Low Voltage	V _{IL}	$V_{OUT} = 4.5V$ $V_{OUT} = 9.0V$ $V_{OUT} = 13.5V$ $ I_{OUT} < 1\mu A$	5 10 15	 - -	1.0 2.0 3.0		_ _ _	1.0 2.0 3.0	— — —	1.0 2.0 3.0	V
Input H Level Current L Level	liH liL	V _{IH} = 18V V _{IL} = 0V	18 18	_	0.1 -0.1		10 ⁻⁵			1.0 - 1.0	μΑ
Quiescent Device Current	l _{DD}	$V_{IN} = V_{SS}$, V_{DD}	5 10 15	_ _ _	0.25 0.5 1.0	_ _ _	0.001 0.001 0.002	0.5	_ _ _	7.5 15 30	μΑ

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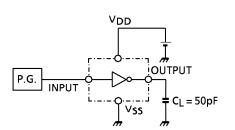
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DYNAMIC ELECTRICAL CHARACTERISTICS (Ta = 25°C, V_{SS} = 0V, C_L = 50pF)

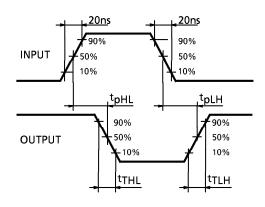
CHARACTERISTIC	SYMBOL	TEST CONDITION	V _{DD} (V)	MIN.	TYP.	MAX.	UNIT	
Output Transition Time			5	_	70	200		
·	tTLH	_	10	_	35	100		
(Low to High)			15	_	30	80	1	
Output Transition Time			5	_	70	200	ns	
Output Transition Time (High to Low)	tTHL	_	10	_	35	100		
			15	_	30	80		
	t _{pLH}		5	_	55	110		
Propagation Delay Time		<u> </u>	10	_	30	60		
			15	_	25	50		
	t _{pHL}		5	_	55	110	ns	
Propagation Delay Time		_	10	_	30	60		
			15	_	25	50		
Input Capacitance	CIN	_	_	7.5	15	рF		

CIRCUIT AND WAVEFORM FOR MEASUREMENT OF DYNAMIC CHARACTERISTICS

TEST CIRCUIT



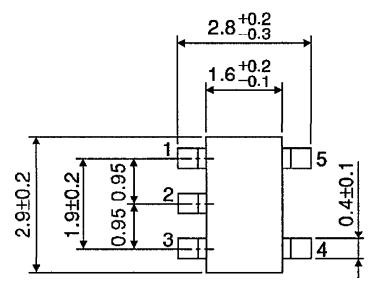
WAVEFORM

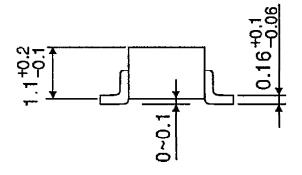


OUTLINE DRAWING

SSOP5-P-0.95







Weight: 0.016g (Typ.)